VRW-56 SQS Silicon PNP transistor in a SOT-23 Plastic Package.

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Low frequency.

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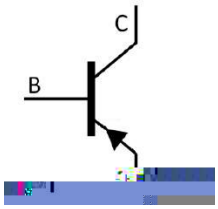
Low frequency power amplifier.

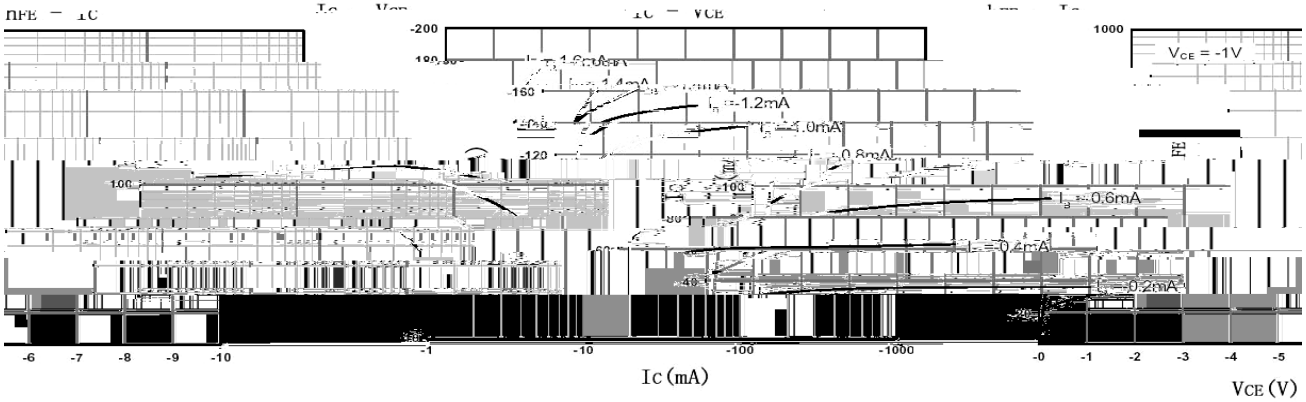


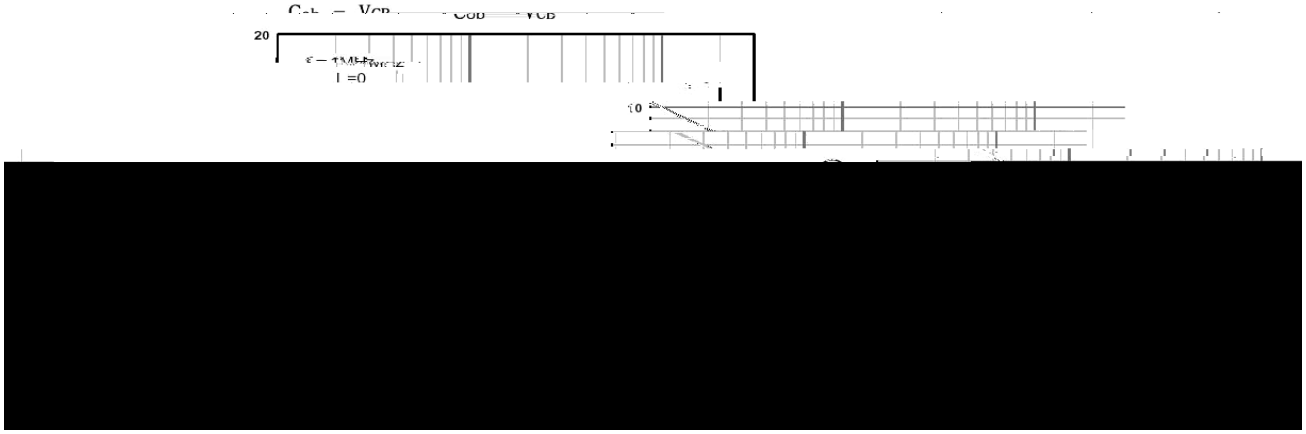
PIN 1 Base PIN 2 Emitter PIN 3 Collector

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-500	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

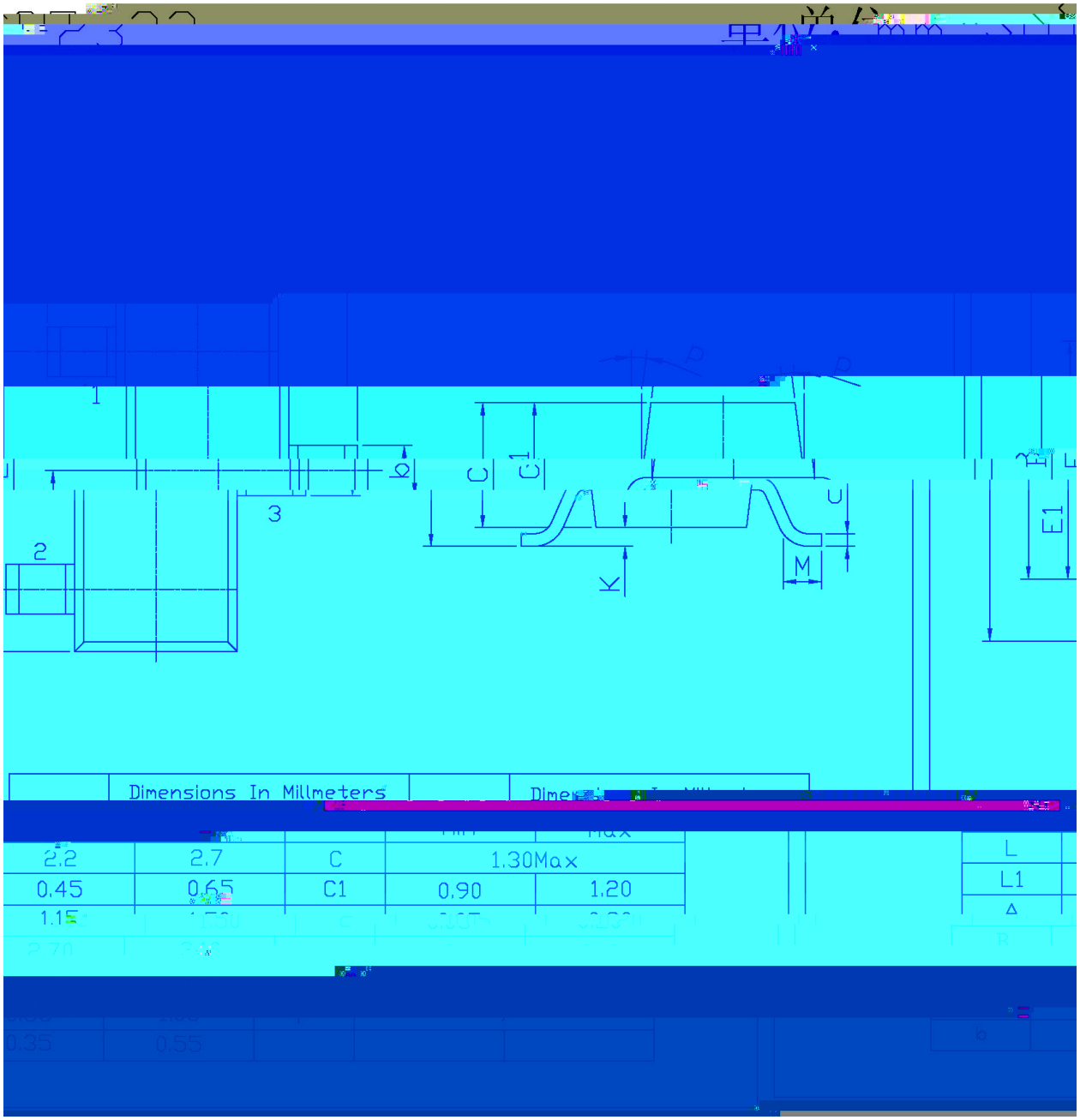
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-35V I_E=0			-0.1	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-5.0V I_C=0			-0.1	A
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-100mA	70		240	
	$h_{FE(2)}$	V_{CE}=-6.0V I_C=-400mA	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA I_B=-10mA		-0.1	-0.25	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-100mA V_{CE}=-1.0V		-0.8	-1.0	V
Transition Frequency	f_T	I_C=-20mA V_{CE}=-6.0V		200		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-6.0V I_E=0 f=1.0MHz				

/ Electrical Characteristic Curve

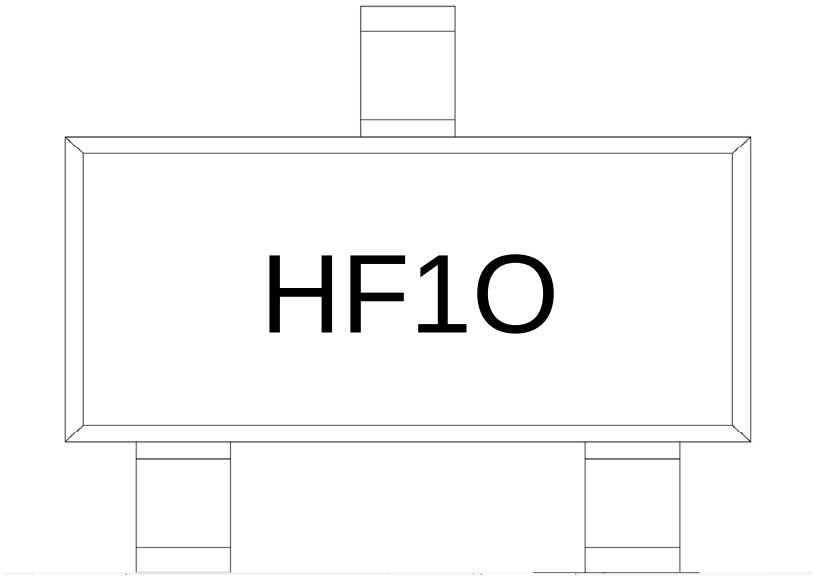




/ Package Dimensions



/ Marking Instructions



H	И
I 4	N
R	h_{IH}

Note:

H	Company Code
F1	Product Type Code
O	h_{FE} Classifications Symbol Code

( ) / Temperature Profile for IR Reflow Soldering(Pb Z